E·XFL



Welcome to E-XFL.COM

Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e300c4s
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	800MHz
Co-Processors/DSP	Security; SEC 3.0
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	SATA 3Gbps (2)
USB	USB 2.0 + PHY (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 125°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	689-BBGA Exposed Pad
Supplier Device Package	689-TEPBGA II (31x31)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8377ecvrang

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

controller, dual I²C controllers, a 4-channel DMA controller, an enhanced secured digital host controller, and a general-purpose I/O port. This figure shows the block diagram of the chip.



Figure 1. MPC8377E Block Diagram and Features

The following features are supported in the chip:

- e300c4s core built on Power Architecture® technology with 32 KB instruction cache and 32 KB data cache, a floating point unit, and two integer units
- DDR1/DDR2 memory controller supporting a 32/64-bit interface
- Peripheral interfaces, such as a 32-bit PCI interface with up to 66-MHz operation
- 32-bit local bus interface running up to 133-MHz
- USB 2.0 (full/high speed) support
- Power management controller for low-power consumption
- High degree of software compatibility with previous-generation PowerQUICC processor-based designs for backward compatibility and easier software migration
- Optional security engine provides acceleration for control and data plane security protocols

The optional security engine (SEC 3.0) is noted with the extension "E" at the end. It allows CPU-intensive cryptographic operations to be offloaded from the main CPU core. The security-processing accelerator provides hardware acceleration for the DES, 3DES, AES, SHA-1, and MD-5 algorithms.

1.3 Dual Enhanced Three-Speed Ethernet Controllers (eTSECs)

The eTSECs include the following features:

- Two enhanced Ethernet interfaces can be used for RGMII/MII/RMII/RTBI
- Two controllers conform to IEEE Std 802.3[®], IEEE 802.3^u, IEEE 802.3^x, IEEE 802.3^z, IEEE 802.3^a, IEEE 802.3^a, and IEEE Std 1588TM standards
- Support for Wake-on-Magic PacketTM, a method to bring the device from standby to full operating mode
- MII management interface for external PHY control and status

1.4 Integrated Programmable Interrupt Controller (IPIC)

The integrated programmable interrupt controller (IPIC) implements the necessary functions to provide a flexible solution for general-purpose interrupt control. The IPIC programming model is compatible with the MPC8260 interrupt controller, and it supports 8 external and 34 internal discrete interrupt sources. Interrupts can also be redirected to an external interrupt controller.

1.5 Power Management Controller (PMC)

The power management controller includes the following features:

- Provides power management when the device is used in both host and agent modes
- Supports PCI Power Management 1.2 D0, D1, D2, and D3hot states
- Support for PME generation in PCI agent mode, PME detection in PCI host mode
- Supports Wake-on-LAN (Magic Packet), USB, GPIO, and PCI (PME input as host)
- Supports MPC8349E backward-compatibility mode

1.6 Serial Peripheral Interface (SPI)

The serial peripheral interface (SPI) allows the device to exchange data between other PowerQUICC family chips, Ethernet PHYs for configuration, and peripheral devices such as EEPROMs, real-time clocks, A/D converters, and ISDN devices.

The SPI is a full-duplex, synchronous, character-oriented channel that supports a four-wire interface (receive, transmit, clock, and slave select). The SPI block consists of transmitter and receiver sections, an independent baud-rate generator, and a control unit.

1.7 DMA Controller, Dual I²C, DUART, Enhanced Local Bus Controller (eLBC), and Timers

The device provides an integrated four-channel DMA controller with the following features:

- Allows chaining (both extended and direct) through local memory-mapped chain descriptors (accessible by local masters)
- Supports misaligned transfers

1.10 PCI Express Controller

The PCI Express controller includes the following features:

- PCI Express 1.0a compatible
- Two $\times 1$ links or one $\times 2$ link width
- Auto-detection of number of connected lanes
- Selectable operation as root complex or endpoint
- Both 32- and 64-bit addressing
- 128-byte maximum payload size
- Support for MSI and INTx interrupt messages
- Virtual channel 0 only
- Selectable Traffic Class
- Full 64-bit decode with 32-bit wide windows
- Dedicated four channel descriptor-based DMA engine per interface

1.11 Serial ATA (SATA) Controllers

The serial ATA (SATA) controllers have the following features:

- Supports Serial ATA Rev 2.5 Specification
- Spread spectrum clocking on receive
- Asynchronous notification
- Hot Plug including asynchronous signal recovery
- Link power management
- Native command queuing
- Staggered spin-up and port multiplier support
- Port multiplier support
- SATA 1.5 and 3.0 Gb/s operation
- Interrupt driven
- Power management support
- Error handling and diagnostic features
 - Far end/near end loopback
 - Failed CRC error reporting
 - Increased ALIGN insertion rates
- Scrambling and CONT override

Characteristic		Symbol	Recommended Value	Unit	Note
SerDes	up to 667 MHz	L[1,2]_ <i>n</i> V _{DD}	1.0 ± 50 mV	۷	1, 3
	800 MHz		1.05 V ± 50 mV	V	1, 3
Operating temperature range	commerical	T _a T _j	T _a =0 (min)— T _j =125 (max)	°C	_
	extended temperature	T _a T _j	T _a =–40 (min)— T _j =125 (max)	°C	_

Table 3. Recommended Operating Conditions (continued)

Notes:

- 1. GV_{DD}, OV_{DD}, AV_{DD}, and V_{DD} must track each other and must vary in the same direction—either in the positive or negative direction.
- 2. AV_{DD} is the input to the filter discussed in Section 25.1, "PLL Power Supply Filtering," and is not necessarily the voltage at the AVDD pin.
- 3. $L[1,2]_nV_{DD}$, SDAV_{DD_0}, XCOREV_{DD}, and XPADV_{DD} power inputs.

This figure shows the undershoot and overshoot voltages at the interfaces of the device.



Note:

1. Note that $t_{\mbox{interface}}$ refers to the clock period associated with the bus clock interface. 2. Note that with the PCI overshoot allowed (as specified above), the device does not fully comply with the maximum AC ratings and device protection guideline outlined in the PCI Rev. 2.3 Specification (Section 4.2.2.3).

Figure 2. Overshoot/Undershoot Voltage for $GV_{DD}/LV_{DD}/OV_{DD}/LBV_{DD}$

Parameter	Symbol ¹	Min	Мах	Unit	Note
MDQS epilogue end	t _{DDKHME}	-0.6	0.6	ns	6, 8

Table 21. DDR1 and DDR2 SDRAM Output AC Timing Specifications (continued)

Notes:

- The symbols used for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state) (reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
 </sub>
- 2. All MCK/MCK referenced measurements are made from the crossing of the two signals ± 0.1 V.
- 3. ADDR/CMD includes all DDR SDRAM output signals except MCK/MCK, MCS, and MDQ//MDM/MDQS.
- 4. Note that t_{DDKHMH} follows the symbol conventions described in Note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK[n] clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. This will typically be set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the MPC8379E PowerQUICC II Pro Host Processor Reference Manual for a description and understanding of the timing modifications enabled by use of these bits.
- 5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data MDQ, ECC, or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the microprocessor.
- 6. All outputs are referenced to the rising edge of MCK*n* at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in Note 1.
- 7. Clock Control register is set to adjust the memory clocks by 1/2 the applied cycle.
- 8. See AN3665, "MPC837xE Design Checklist," for proper DDR termination.

The minimum frequency for DDR2 is 250 MHz data rate (125 MHz clock), 167 MHz data rate (83 MHz clock) for DDR1. This figure shows the DDR1 and DDR2 SDRAM output timing for the MCK to MDQS skew measurement (t_{DDKHMH}).



Figure 4. DDR Timing Diagram for t_{DDKHMH}

This figure shows the DDR1 and DDR2 SDRAM output timing diagram.



Figure 5. DDR1 and DDR2 SDRAM Output Timing Diagram

This figure provides AC test load for the DDR bus.



Figure 6. DDR AC Test Load

7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the chip.

7.1 DUART DC Electrical Characteristics

This table provides the DC electrical characteristics for the DUART interface of the device.

Table 22. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Мах	Unit
High-level input voltage	V _{IH}	2	OV _{DD} + 0.3	V
Low-level input voltage OV _{DD}	V _{IL}	-0.3	0.8	V
High-level output voltage, I _{OH} = −100 μA	V _{OH}	OV _{DD} - 0.2		V

Parameter	Symbol	Min	Мах	Unit
Low-level output voltage, $I_{OL} = 100 \ \mu A$	V _{OL}	_	0.2	V
Input current, (0 $V \leq V_{IN} \leq OV_{DD}$)	I _{IN}	—	±30	μΑ

Table 22. DUART DC Electrical Characteristics (continued)

Note: The symbol V_{IN} , in this case, represents the OV_{IN} symbol referenced in Table 2.

7.2 DUART AC Electrical Specifications

this table provides the AC timing parameters for the DUART interface of the device.

Table 23. DUART AC Timing Specifications

Parameter	Value	Unit	Note
Minimum baud rate	256	baud	—
Maximum baud rate	> 1,000,000	baud	1
Oversample rate	16	_	2

Notes:

1. Actual attainable baud rate will be limited by the latency of interrupt processing.

2. The middle of a start bit is detected as the 8th sampled 0 after the 1-to-0 transition of the start bit. Subsequent bit values are sampled each 16th sample.

8 Ethernet: Enhanced Three-Speed Ethernet (eTSEC)

This section provides the AC and DC electrical characteristics for the enhanced three-speed Ethernet controller.

8.1 Enhanced Three-Speed Ethernet Controller (eTSEC) (10/100/1000 Mbps)—MII/RGMII/RTBI/RMII DC Electrical Characteristics

The electrical characteristics specified here apply to media independent interface (MII), reduced gigabit media independent interface (RGMII), reduced ten-bit interface (RTBI), reduced media independent interface (RMII) signals, management data input/output (MDIO) and management data clock (MDC).

The MII and RMII interfaces are defined for 3.3 V, while the RGMII and RTBI interfaces can be operated at 2.5 V. The RGMII and RTBI interfaces follow the *Reduced Gigabit Media-Independent Interface* (*RGMII*) Specification Version 1.3. The RMII interface follows the *RMII Consortium RMII Specification Version 1.2*.

8.1.1 MII, RMII, RGMII, and RTBI DC Electrical Characteristics

MII and RMII drivers and receivers comply with the DC parametric attributes specified in Table 24 and Table 25. The RGMII and RTBI signals in Table 25 are based on a 2.5 V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Parameter	Symbol	Min	Max	Unit	Note
Supply voltage 3.3 V	LV _{DD1} LV _{DD2}	3.13	3.47	V	1
Output high voltage (LV _{DD1} /LV _{DD2} = Min, I _{OH} = -4.0 mA)	V _{OH}	2.40	LV _{DD1} /LV _{DD2} + 0.3	V	—
Output low voltage (LV _{DD1} /LV _{DD2} = Min, I _{OL} = 4.0 mA)	V _{OL}	GND	0.50	V	—
Input high voltage	V _{IH}	2.0	$LV_{DD1}/LV_{DD2} + 0.3$	V	—
Input low voltage	V _{IL}	-0.3	0.90	V	—
Input high current $(V_{IN} = LV_{DD1}, V_{IN} = LV_{DD2})$	Ι _{ΙΗ}	—	30	μA	1
Input low current (V _{IN} = GND)	IIL	-600	_	μA	

Table 24. MII and RMII DC Electrical Characteristics

Notes:

1. LV_{DD1} supports eTSEC 1. LV_{DD2} supports eTSEC 2.

Parameter	Symbol	Min	Мах	Unit	Note
Supply voltage 2.5 V	LV _{DD1} LV _{DD2}	2.37	2.63	V	1
Output high voltage (LV _{DD1} /LV _{DD2} = Min, IOH = -1.0 mA)	V _{OH}	2.00	$LV_{DD1}/LV_{DD2} + 0.3$	V	_
Output low voltage (LV _{DD1} /LV _{DD2} = Min, I _{OL} = 1.0 mA)	V _{OL}	GND – 0.3	0.40	V	_
Input high voltage	V _{IH}	1.7	$LV_{DD1}/LV_{DD2} + 0.3$	V	_
Input low voltage	V _{IL}	-0.3	0.70	V	_
Input high current (V _{IN} = LV _{DD1} , V _{IN} = LV _{DD2})	Iн	—	-20	μA	1
Input low current (V _{IN} = GND)	IIL	-20	_	μA	—

Table 25. RGMII and RTBI DC Electrical Characteristics

Notes:

1. LV_{DD1} supports eTSEC 1. LV_{DD2} supports eTSEC 2.

This figure shows the RMII receive AC timing diagram.



Figure 14. RMII Receive AC Timing Diagram

8.3 Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock).

This figure provides the AC test load for eTSEC.



Figure 15. eTSEC AC Test Load

8.3.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 2.5 V or 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in Table 31 and Table 32.

Parameter	Conditions		Symbol	Min	Мах	Unit
Supply voltage (2.5 V)		_	LV _{DD1}	2.37	2.63	V
Output high voltage	I _{OH} = -1.0 mA	LV _{DD1} = Min	V _{OH}	2.00	LV _{DD1} + 0.3	V
Output low voltage	I _{OL} = 1.0 mA	LV _{DD1} = Min	V _{OL}	GND – 0.3	0.40	V
Input high voltage	—	LV _{DD1} = Min	V _{IH}	1.7	—	V
Input low voltage	—	LV _{DD1} = Min	V _{IL}	-0.3	0.70	V
Input high current	VI	$_{\rm N} = {\rm LV}_{\rm DD1}$	I _{IH}	—	20	μA
Input low current	VI	$_{\rm N} = {\rm LV}_{\rm DD1}$	IIL	-15	—	μA

This table describes the general timing parameters of the local bus interface of the device when in PLL bypass mode.

Parameter	Symbol ¹	Min	Max	Unit	Note
Local bus cycle time	t _{LBK}	15	_	ns	2
Input setup to local bus clock	t _{LBIVKH}	7.0	_	ns	3, 4
Input hold from local bus clock	t _{LBIXKH}	1.0	_	ns	3, 4
LALE output fall to LAD output transition (LATCH hold time)	t _{LBOTOT1}	1.5	_	ns	5
LALE output fall to LAD output transition (LATCH hold time)	t _{LBOTOT2}	3.0	_	ns	6
LALE output fall to LAD output transition (LATCH hold time)	t _{LBOTOT3}	2.5	_	ns	7
Local bus clock to LALE rise	t _{LBKHLR}	_	4.5	ns	_
Local bus clock to output valid	t _{LBKHOV}	_	3.0	ns	3
Local bus clock to output high impedance for LAD/LDP	t _{LBKHOZ}	_	4.0	ns	3, 8

Table 40. Local Bus General Timing Parameters—PLL Bypass Mode

Notes:

 The symbols used for timing specifications herein follow the pattern of t_{(First two letters of functional block)(signal)(state)} (reference)(state) for inputs and t_(First two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{LBIXKH1} symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the output (O) going invalid (X) or output hold time.

- All timings are in reference to falling edge of LCLK0 (for all outputs and for LGTA and LUPWAIT inputs) or rising edge of LCLK0 (for all other inputs).
- 3. All signals are measured from LBV_{DD}/2 of the rising/falling edge of LCLK0 to $0.4 \times LBV_{DD}$ of the signal in question for 3.3-V signaling levels.
- 4. Input timings are measured at the pin.
- 5. t_{LBOTOT1} should be used when LBCR[AHD] is set and the load on LALE output pin is at least 10pF less than the load on LAD output pins.
- t_{LBOTOT2} should be used when LBCR[AHD] is not set and the load on LALE output pin is at least 10pF less than the load on LAD output pins.
- 7. t_{LBOTOT3} should be used when LBCR[AHD] is not set and the load on LALE output pin equals to the load on LAD output pins.
- 8. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.

This figure provides the AC test load for the local bus.



Figure 19. Local Bus AC Test Load

This figures show the local bus signals.



Figure 20. Local Bus Signals, Non-special Signals Only (PLL Enable Mode)

11.2.2.2 Full-Speed Read Meeting Hold (Minimum Delay)

There is no minimum delay constraint due to the full clock cycle between the driving and sampling of data.

$t_{CLK_DELAY} + t_{OH} + t_{DATA_DELAY} > t_{SFSIXKH}$

Eqn. 9

This means that Data + Clock delay must be greater than -2 ns. This is always fulfilled.

11.3 eSDHC AC Timing Specifications (High-Speed Mode)

This table provides the eSDHC AC timing specifications for high-speed mode as defined in Figure 30 and Figure 31.

Table 43. eSDHC AC Timing Specifications for High-Speed Mode

At recommended operating conditions OV_{DD} = 3.3 V \pm 165 mV.

Parameter	Symbol ¹	Min	Мах	Unit	Note
SD_CLK clock frequency—high speed mode	f _{SHSCK}	0	50	MHz	_
SD_CLK clock cycle	t _{SHSCK}	20	—	ns	_
SD_CLK clock frequency—identification mode	f _{SIDCK}	0	400	KHz	_
SD_CLK clock low time	t _{SHSCKL}	7	—	ns	2
SD_CLK clock high time	t _{SHSCKH}	7	—	ns	2
SD_CLK clock rise and fall times	t _{SHSCKR∕} t _{SHSCKF}	_	3	ns	2
Input setup times: SD_CMD, SD_DATx, SD_CD to SD_CLK	t _{SHSIVKH}	5	—	ns	2
Input hold times: SD_CMD, SD_DATx, SD_CD to SD_CLK	t _{SHSIXKH}	0	—	ns	2
Output delay time: SD_CLK to SD_CMD, SD_DATx valid	t _{SHSKHOV}	_	4	ns	2
Output Hold time: SD_CLK to SD_CMD, SD_DATx invalid	t _{SHSKHOX}	0	—	ns	2
SD_CLK delay within device	t _{INT_CLK_DLY}	1.5	—	ns	4
SD Card Input Setup	t _{ISU}	6	—	ns	3
SD Card Input Hold	t _{IH}	2	—	ns	3
SD Card Output Valid	t _{ODLY}	_	14	ns	3
SD Card Output Hold	t _{OH}	2.5		ns	3

Notes:

1. The symbols used for timing specifications herein follow the pattern of t_{(first three letters of functional block)(signal)(state)} (reference)(state) for inputs and t_(first three letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{SFSIXKH} symbolizes eSDHC full mode speed device timing (SFS) input (I) to go invalid (X) with respect to the clock reference (K) going to high (H). Also t_{SFSKHOV} symbolizes eSDHC full speed timing (SFS) for the clock reference (K) to go high (H), with respect to the output (O) going valid (V) or data output valid time. Note that, in general, the clock reference symbol representation is based on five letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

2. Measured at capacitive load of 40 pF.

3. For reference only, according to the SD card specifications.

4. Average, for reference only.

This means that data delay should be equal or less than the clock delay in the ideal case where $t_{SHSCLKL} = 10$ ns:

```
t_{DATA\_DELAY} - t_{CLK\_DELAY} < 10 - 6 - 4t_{DATA\_DELAY} - t_{CLK\_DELAY} < 0
```

11.3.1.2 High-Speed Write Meeting Hold (Minimum Delay)

The following equations show how to calculate the allowed skew range between the SD_CLK and SD_DAT/CMD signals on the PCB.

```
t_{CLK\_DELAY} < t_{SHSCKL} + t_{SHSKHOX} + t_{DATA\_DELAY} - t_{IH} Eqn. 13
```

$$t_{CLK_DELAY} - t_{DATA_DELAY} < t_{SHSCKL} + t_{SHSKHOX} - t_{IH}$$
 Eqn. 14

This means that clock can be delayed versus data up to 8 ns (external delay line) in ideal case of $t_{SHSCLKL} = 10$ ns:

```
t_{CLK\_DELAY} - t_{DATA\_DELAY} < 10 + 0 - 2
t_{CLK\_DELAY} - t_{DATA\_DELAY} < 8
```

11.3.2 High-Speed Input Path (Read)

This figure provides the data and command input timing diagram.



Figure 31. High-Speed Input Path

For the input path, the device eSDHC expects to sample the data 1.5 internal clock cycles after it was driven by the SD card. Since in this mode the SD card drives the data at the rising edge of the clock, a sufficient delay to the clock and the data must exist to ensure it will not be sampled at the wrong internal

This figure provides the boundary-scan timing diagram.



Figure 35. Boundary-Scan Timing Diagram

This figure provides the test access port timing diagram.



VM = Midpoint Voltage (OVDD/2)



Table 49. PCI AC Timing Specifications at 66 MHz (continued)

PCI_SYNC_IN clock input levels are with next levels: VIL = $0.1 \times OV_{DD}$, VIH = $0.7 \times OV_{DD}$.

Parameter	Symbol ¹	Min	Мах	Unit	Note
Input hold from cock	t _{PCIXKH}	0.25	—	ns	2, 4, 6
Output clock skew	t _{PCKOSK}	_	0.5	ns	5

Notes:

Note that the symbols used for timing specifications herein follow the pattern of t_{(first two letters of functional block)(signal)(state)} (reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{PCIVKH} symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the PCI_SYNC_IN clock, t_{SYS}, reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.

2. See the timing measurement conditions in the PCI 2.3 Local Bus Specifications.

- 3. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
- 4. Input timings are measured at the pin.
- 5. PCI specifications allows 1 ns skew for 66 MHz but includes the total allowed skew, board, connectors, etc.
- 6. Value does not comply with the PCI 2.3 Local Bus Specifications.

This table shows the PCI AC timing specifications at 33 MHz.

Table 50. PCI AC Timing Specifications at 33 MHz

PCI_SYNC_IN clock input levels are with next levels: VIL = $0.1 \times OV_{DD}$, $V_{IH} = 0.7 \times OV_{DD}$.

Parameter	Symbol ¹	Min	Мах	Unit	Note
Clock to output valid	t _{PCKHOV}	—	11	ns	2
Output hold from clock	t _{PCKHOX}	2	—	ns	2
Clock to output high impedance	t _{PCKHOZ}	—	14	ns	2, 3
Input setup to clock	t _{PCIVKH}	3.0	—	ns	2, 4
Input hold from clock	t _{PCIXKH}	0.25	—	ns	2, 4, 6
Output clock skew	t _{PCKOSK}	_	0.5	ns	5

Notes:

- Note that the symbols used for timing specifications herein follow the pattern of t_{(first two letters of functional block)(signal)(state)} (reference)(state) for inputs and t_(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{PCIVKH} symbolizes PCI timing (PC) with respect to the time the input signals (I) reach the valid state (V) relative to the PCI_SYNC_IN clock, t_{SYS}, reference (K) going to the high (H) state or setup time. Also, t_{PCRHFV} symbolizes PCI timing (PC) with respect to the time hard reset (R) went high (H) relative to the frame signal (F) going to the valid (V) state.
- 2. See the timing measurement conditions in the PCI 2.3 Local Bus Specifications.
- 3. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
- 4. Input timings are measured at the pin.
- 5. PCI specifications allows 2 ns skew for 33 MHz but includes the total allowed skew, board, connectors, etc.
- 6. Value does not comply with the PCI 2.3 Local Bus Specifications.

The eye diagram must be valid for any 250 consecutive UIs.

A recovered Tx UI is calculated over 3500 consecutive unit intervals of sample data. The eye diagram is created using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the Tx UI.

NOTE

It is recommended that the recovered Tx UI be calculated using all edges in the 3500 consecutive UI interval with a fit algorithm using a minimization merit function (that is, least squares and median deviation fits).



Figure 42. Minimum Transmitter Timing and Voltage Output Compliance Specifications

15.4.3 Differential Receiver (Rx) Input Specifications

This table defines the specifications for the differential input at all receivers. The parameters are specified at the component pins.

Parameter	Comments	Symbol	Min	Typical	Max	Units	Note
Unit interval	Each U_{PERX} is 400 ps ± 300 ppm. U_{PERX} does not account for Spread Spectrum Clock dictated variations.	UI	399.88	400	400.12	ps	1
Differential peak-to-peak output voltage	$V_{PEDPPRX} = 2 \times V_{RX-D+} - V_{RX-D-} $	V _{RX-DIFFp-p}	0.175	—	1.200	V	2

Table 53. Differential Receiver (Rx) Input Specifications

Parameter	Comments	Symbol	Min	Typical	Max	Units	Note
Minimum receiver eye width	The maximum interconnect media and transmitter jitter that can be tolerated by the receiver can be derived as $T_{RX-MAX-JITTER} = 1 -$ $U_{PEEWRX} = 0.6$ UI.	T _{RX-EYE}	0.4			UI	2, 3
Maximum time between the jitter median and maximum deviation from the median.	Jitter is defined as the measurement variation of the crossing points ($V_{PEDPPRX} = 0$ V) in relation to a recovered Tx UI. A recovered Tx UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the Tx UI.	T _{RX-EYE-MEDIAN-to} -MAX-JITTER			0.3	UI	2, 3, 7
AC peak common mode input voltage	$V_{PEACPCMRX} = V_{RXD+} - V_{RXD-l/2} - V_{RX-CM-DC} \\V_{RX-CM-DC} = DC_{(avg)} \text{ of } V_{RX-D+} - V_{RX-D-l/2} /2$	V _{RX-CM-ACp}	—	_	150	mV	2
Differential return loss	Measured over 50 MHz to 1.25 GHz with the D+ and D– lines biased at +300 mV and –300 mV, respectively.	RL _{RX-DIFF}	10	_	—	dB	4
Common mode return loss	Measured over 50 MHz to 1.25 GHz with the D+ and D- lines biased at 0 V.	RL _{RX-CM}	6	_	_	dB	4
DC differential input impedance	RX DC differential mode impedance.	Z _{RX-DIFF-DC}	80	100	120	Ω	5
DC Input Impedance	Required RX D+ as well as D- DC impedance (50 \pm 20% tolerance).	Z _{RX-DC}	40	50	60	Ω	2, 5
Powered down DC input impedance	Required RX D+ as well as D– DC impedance when the receiver terminations do not have power.	Z _{RX-HIGH-IMP-DC}	200 k	_	_	Ω	6
Electrical idle detect threshold	$V_{PEEIDT} = 2 \times V_{RX-D+} - V_{RX-D-} $ Measured at the package pins of the receiver	V _{RX-IDLE-DET-DIFF} p-p	65	—	175	mV	—

driver chip manufacturer to verify whether this connection scheme is compatible with a particular clock driver chip.



Figure 58. AC-Coupled Differential Connection with LVPECL Clock Driver (Reference Only)

This figure shows the SerDes reference clock connection reference circuits for a single-ended clock driver. It assumes the DC levels of the clock driver are compatible with device SerDes reference clock input's DC requirement.



21.2.4 AC Requirements for SerDes Reference Clocks

The clock driver selected should provide a high quality reference clock with low phase noise and cycle-to-cycle jitter. Phase noise less than 100 KHz can be tracked by the PLL and data recovery loops and is less of a problem. Phase noise above 15 MHz is filtered by the PLL. The most problematic phase noise

The thermal performance of a device cannot be adequately predicted from the junction to ambient thermal resistance. The thermal performance of any component is strongly dependent on the power dissipation of surrounding components. In addition, the ambient temperature varies widely within the application. For many natural convection and especially closed box applications, the board temperature at the perimeter (edge) of the package is approximately the same as the local air temperature near the device. Specifying the local ambient conditions explicitly as the board temperature provides a more precise description of the local ambient conditions that determine the temperature of the device.

At a known board temperature, the junction temperature is estimated using the following equation:

$$T_J = T_A + (R_{\theta JB} \times P_D)$$
 where:

 T_A = ambient temperature for the package (°C) $R_{\theta JB}$ = junction to board thermal resistance (°C/W) per JESD51-8 P_D = power dissipation in the package (W)

When the heat loss from the package case to the air can be ignored, acceptable predictions of junction temperature can be made. The application board should be similar to the thermal test condition: the component is soldered to a board with internal planes.

24.2.3 Experimental Determination of Junction Temperature

NOTE

The heat sink cannot be mounted on the package.

To determine the junction temperature of the device in the application after prototypes are available, use the thermal characterization parameter (Ψ_{JT}) to determine the junction temperature and a measure of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D)$$

where:

 T_J = junction temperature (°C)

 T_T = thermocouple temperature on top of package (°C)

 Ψ_{JT} = junction to ambient thermal resistance (°C/W)

 P_D = power dissipation in the package (W)

The thermal characterization parameter is measured per the JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

24.2.4 Heat Sinks and Junction-to-Case Thermal Resistance

For the power values the device is expected to operate at, it is anticipated that a heat sink will be required. A preliminary estimate of heat sink performance can be obtained from the following first-cut approach.

Tyco Electronics Chip Coolers[™] www.chipcoolers.com

Wakefield Engineering www.wakefield.com

Interface material vendors include the following:

Chomerics, Inc. www.chomerics.com

Dow-Corning Corporation Dow-Corning Electronic Materials www.dowcorning.com

Shin-Etsu MicroSi, Inc. www.microsi.com

The Bergquist Company www.bergquistcompany.com

24.3 Heat Sink Attachment

The device requires the use of heat sinks. When heat sinks are attached, an interface material is required, preferably thermal grease and a spring clip. The spring clip should connect to the printed circuit board, either to the board itself, to hooks soldered to the board, or to a plastic stiffener. Avoid attachment forces that can lift the edge of the package or peel the package from the board. Such peeling forces reduce the solder joint lifetime of the package. The recommended maximum compressive force on the top of the package is 10 lb force (4.5 kg force). Any adhesive attachment should attach to painted or plastic surfaces, and its performance should be verified under the application requirements.

24.3.1 Experimental Determination of the Junction Temperature with a Heat Sink

When a heat sink is used, the junction temperature is determined from a thermocouple inserted at the interface between the case of the package and the interface material. A clearance slot or hole is normally required in the heat sink. Minimize the size of the clearance to minimize the change in thermal performance caused by removing part of the thermal interface to the heat sink. Because of the experimental difficulties with this technique, many engineers measure the heat sink temperature and then back calculate the case temperature using a separate measurement of the thermal resistance of the interface. From this case temperature, the junction temperature is determined from the junction to case thermal resistance.

 $T_J = T_C + (R_{\theta JC} \times P_D)$ where:

 T_J = junction temperature (°C) T_C = case temperature of the package (°C)